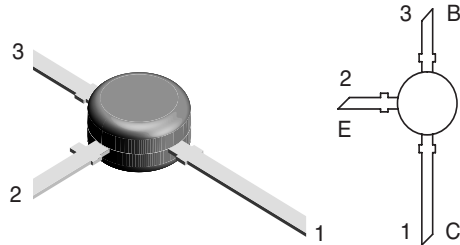


Silicon NPN Planar RF Transistor

Features

- High power gain
- Low noise figure
- High transition frequency
- Lead (Pb)-free component
- Component in accordance to RoHS 2002/95/EC and WEEE 2002/96/EC



19039

Applications

RF amplifier up to GHz range specially for wide band antenna amplifier.



Electrostatic sensitive device.
Observe precautions for handling.

Mechanical Data

Case: TO-50 Plastic case

Weight: approx. 111 mg

Pinning: 1 = Collector, 2 = Emitter, 3 = Base

Parts Table

Part	Ordering code	Marking	Remarks	Package
BFR91A	BFR91AGELB-GS08	BFR91A	Packed in Bulk	TO-50(3)

Absolute Maximum Ratings

$T_{amb} = 25\text{ }^{\circ}\text{C}$, unless otherwise specified

Parameter	Test condition	Symbol	Value	Unit
Collector-base voltage		V_{CBO}	20	V
Collector-emitter voltage		V_{CEO}	12	V
Emitter-base voltage		V_{EBO}	2	V
Collector current		I_C	50	mA
Total power dissipation	$T_{amb} \leq 60\text{ }^{\circ}\text{C}$	P_{tot}	300	mW
Junction temperature		T_j	150	$^{\circ}\text{C}$
Storage temperature range		T_{stg}	- 65 to + 150	$^{\circ}\text{C}$

Maximum Thermal Resistance

Parameter	Test condition	Symbol	Value	Unit
Junction ambient	¹⁾	R_{thJA}	300	K/W

¹⁾ on glass fibre printed board (40 x 25 x 1.5) mm³ plated with 35 μm Cu

Electrical DC Characteristics

$T_{amb} = 25\text{ }^{\circ}\text{C}$, unless otherwise specified

Parameter	Test condition	Symbol	Min	Typ.	Max	Unit
Collector-emitter cut-off current	$V_{CE} = 20\text{ V}$, $V_{BE} = 0$	I_{CES}			100	μA
Collector-base cut-off current	$V_{CB} = 20\text{ V}$, $I_E = 0$	I_{CBO}			100	nA
Emitter-base cut-off current	$V_{EB} = 2\text{ V}$, $I_C = 0$	I_{EBO}			10	μA
Collector-emitter breakdown voltage	$I_C = 1\text{ mA}$, $I_B = 0$	$V_{(BR)CEO}$	12			V
Collector-emitter saturation voltage	$I_C = 50\text{ mA}$, $I_B = 5\text{ mA}$	V_{CEsat}		0.1	0.4	V
DC forward current transfer ratio	$V_{CE} = 5\text{ V}$, $I_C = 30\text{ mA}$	h_{FE}	40	90	150	

Electrical AC Characteristics

$T_{amb} = 25\text{ }^{\circ}\text{C}$, unless otherwise specified

Parameter	Test condition	Symbol	Min	Typ.	Max	Unit
Transition frequency	$V_{CE} = 5\text{ V}$, $I_C = 30\text{ mA}$, $f = 500\text{ MHz}$	f_T		6		GHz
Collector-base capacitance	$V_{CB} = 10\text{ V}$, $f = 1\text{ MHz}$	C_{cb}		0.4		pF
Collector-emitter capacitance	$V_{CB} = 5\text{ V}$, $f = 1\text{ MHz}$	C_{ce}		0.3		pF
Emitter-base capacitance	$V_{EB} = 0.5\text{ V}$, $f = 1\text{ MHz}$	C_{eb}		1.5		pF
Noise figure	$V_{CE} = 8\text{ V}$, $Z_S = 50\text{ }\Omega$, $f = 800\text{ MHz}$, $I_C = 5\text{ mA}$	F		1.6		dB
	$V_{CE} = 8\text{ V}$, $Z_S = 50\text{ }\Omega$, $f = 800\text{ MHz}$, $I_C = 30\text{ mA}$	F		2.3		dB
Power gain	$V_{CE} = 8\text{ V}$, $I_C = 30\text{ mA}$, $Z_S = 50\text{ }\Omega$, $Z_L = Z_{Lopt}$, $f = 800\text{ MHz}$	G_{pe}		14		dB
Linear output voltage - two tone intermodulation test	$V_{CE} = 8\text{ V}$, $I_C = 30\text{ mA}$, $d_{IM} = 60\text{ dB}$, $f_1 = 806\text{ MHz}$, $f_2 = 810\text{ MHz}$, $Z_S = Z_L = 50\text{ }\Omega$	$V_1 = V_2$		280		mV
Third order intercept point	$V_{CE} = 8\text{ V}$, $I_C = 30\text{ mA}$, $f = 800\text{ MHz}$	IP_3		32		dBm

Common Emitter S-Parameters

$Z_0 = 50\text{ }\Omega$, $T_{amb} = 25\text{ }^{\circ}\text{C}$, unless otherwise specified

V_{CE}/V	I_C/mA	f/MHz	S11		S21		S12		S22	
			LIN MAG	ANG deg	LIN MAG	ANG deg	LIN MAG	ANG deg	LIN MAG	ANG deg
8	2	100	0.92	-22.1	6.38	162.8	0.02	78.4	0.9	-8.1
		300	0.78	-61.3	5.42	134.7	0.05	61.5	0.88	-20.8
		500	0.64	-92.7	4.38	114.3	0.07	52.8	0.79	-28.2
		800	0.51	-128.0	3.19	92.9	0.09	49.3	0.73	-35.9
		1000	0.45	-146.3	2.65	82.3	0.10	50.4	0.71	-40.6
		1200	0.41	-161.4	2.27	73.8	0.11	53.1	0.70	-45.1
		1500	0.37	177.9	1.85	63.0	0.12	57.8	0.71	-52.3
		1800	0.34	159.7	1.58	53.4	0.14	61.8	0.73	-60.0
8	5	100	0.79	-31.8	13.51	153.5	0.02	75.1	0.92	-13.4



V _{CE} /V	I _C /mA	f/MHz	S11		S21		S12		S22	
			LIN MAG	ANG	LIN MAG	ANG	LIN MAG	ANG	LIN MAG	ANG
				deg		deg		deg		deg
		300	0.54	-78.6	9.24	119.9	0.04	61.9	0.73	-26.4
		500	0.40	-107.8	6.44	101.9	0.06	61.0	0.64	-31.1
		800	0.30	-138.4	4.30	85.7	0.09	63.7	0.59	-36.3
		1000	0.27	-153.8	3.50	77.8	0.10	65.0	0.58	-41.3
		1200	0.25	-167.2	2.98	71.1	0.12	65.7	0.58	-45.8
		1500	0.22	175.1	2.41	62.4	0.14	66.0	0.59	-53.2
		1800	0.21	157.8	2.06	54.2	0.18	65.3	0.61	-60.6
		2000	0.20	149.4	1.88	49.7	0.19	64.5	0.62	-65.5
8	10	100	0.63	-43.0	21.15	143.4	0.02	72.5	0.85	-18.5
		300	0.35	-91.7	11.55	109.2	0.04	67.2	0.62	-28.0
		500	0.25	-117.7	7.47	95.1	0.06	69.5	0.55	-30.6
		800	0.20	-145.2	4.85	82.1	0.09	71.1	0.53	-36.4
		1000	0.18	-160.0	3.93	75.5	0.11	71.1	0.52	-41.3
		1200	0.17	-171.7	3.32	69.8	0.13	70.4	0.52	-45.9
		1500	0.16	173.5	2.70	62.0	0.16	68.7	0.53	-53.7
		1800	0.15	153.9	2.30	54.6	0.19	66.4	0.54	-61.4
		2000	0.15	148.4	2.09	50.3	0.21	64.8	0.55	-66.5
8	20	100	0.44	-55.8	28.24	132.6	0.02	72.8	0.76	-22.3
		300	0.22	-103.9	12.79	102.0	0.04	74.1	0.54	-26.5
		500	0.16	-127.5	8.00	90.7	0.06	75.8	0.50	-28.6
		800	0.14	-153.3	5.13	79.8	0.09	75.4	0.49	-35.2
		1000	0.13	-165.9	4.15	73.9	0.11	74.2	0.48	-40.4
		1200	0.12	-177.3	3.51	68.7	0.13	72.9	0.49	-45.5
		1500	0.12	170.1	2.84	61.5	0.17	70.0	0.50	-53.6
		1800	0.12	152.3	2.42	54.4	0.20	67.1	0.51	-61.6
		2000	0.11	147.1	2.21	50.6	0.22	65.0	0.52	-66.7
8	30	100	0.34	-64.0	31.01	127.3	0.02	73.3	0.71	-23.3
		300	0.17	-112.9	13.08	99.1	0.04	77.2	0.52	-24.9
		500	0.14	-136.2	8.10	88.9	0.06	77.8	0.49	-27.3
		800	0.13	-159.4	5.17	78.7	0.09	76.8	0.48	-34.3
		1000	0.12	-171.4	4.18	73.0	0.11	75.3	0.48	-39.6
		1200	0.12	178.6	3.53	68.0	0.13	73.6	0.48	-45.0
		1500	0.12	165.7	2.87	61.1	0.17	70.5	0.49	-53.3
		1800	0.11	147.8	2.44	54.2	0.20	67.4	0.50	-61.3
		2000	0.11	143.7	2.23	50.3	0.22	65.4	0.51	-66.6

Typical Characteristics (T_{amb} = 25 °C unless otherwise specified)

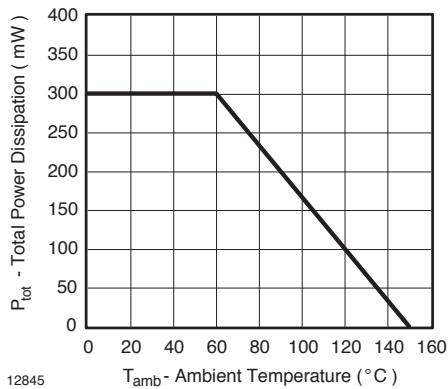


Figure 1. Total Power Dissipation vs. Ambient Temperature

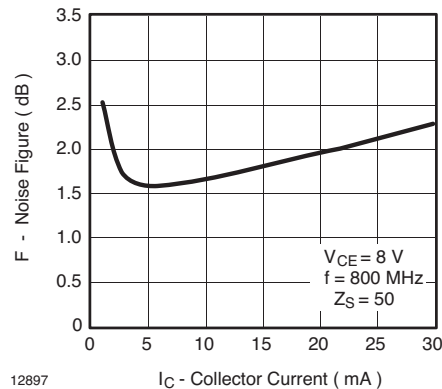


Figure 4. Noise Figure vs. Collector Current

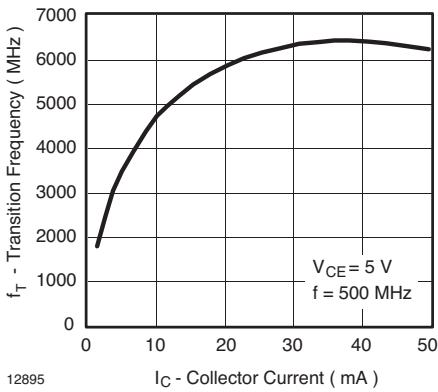


Figure 2. Transition Frequency vs. Collector Current

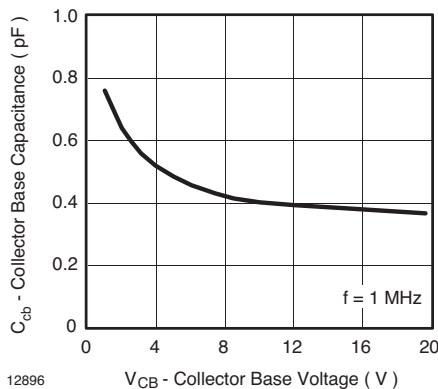


Figure 3. Collector Base Capacitance vs. Collector Base Voltage

$V_{CE} = 10\text{ V}$, $I_C = 10\text{ mA}$, $Z_0 = 50\ \Omega$

S₁₁

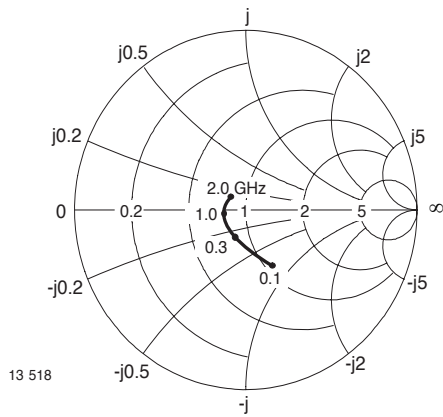


Figure 5. Input Reflection Coefficient

S₁₂

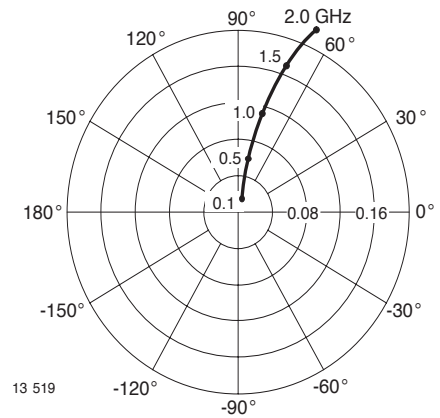


Figure 7. Reverse Transmission Coefficient

S₂₁

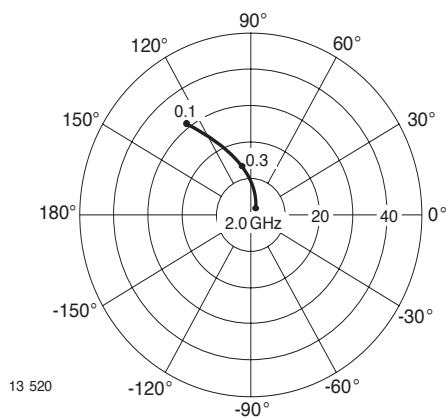


Figure 6. Forward Transmission Coefficient

S₂₂

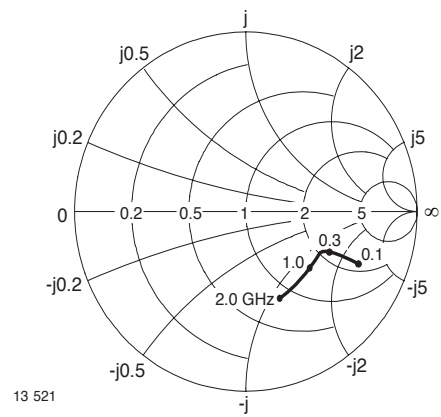
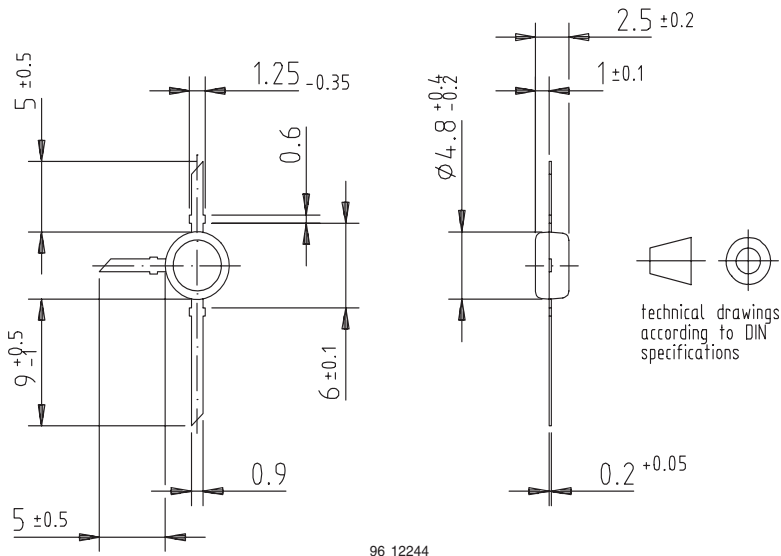


Figure 8. Output Reflection Coefficient

Package Dimensions in mm



96 12244



Ozone Depleting Substances Policy Statement

It is the policy of Vishay Semiconductor GmbH to

1. Meet all present and future national and international statutory requirements.
2. Regularly and continuously improve the performance of our products, processes, distribution and operating systems with respect to their impact on the health and safety of our employees and the public, as well as their impact on the environment.

It is particular concern to control or eliminate releases of those substances into the atmosphere which are known as ozone depleting substances (ODSs).

The Montreal Protocol (1987) and its London Amendments (1990) intend to severely restrict the use of ODSs and forbid their use within the next ten years. Various national and international initiatives are pressing for an earlier ban on these substances.

Vishay Semiconductor GmbH has been able to use its policy of continuous improvements to eliminate the use of ODSs listed in the following documents.

1. Annex A, B and list of transitional substances of the Montreal Protocol and the London Amendments respectively
2. Class I and II ozone depleting substances in the Clean Air Act Amendments of 1990 by the Environmental Protection Agency (EPA) in the USA
3. Council Decision 88/540/EEC and 91/690/EEC Annex A, B and C (transitional substances) respectively.

Vishay Semiconductor GmbH can certify that our semiconductors are not manufactured with ozone depleting substances and do not contain such substances.

We reserve the right to make changes to improve technical design and may do so without further notice.

Parameters can vary in different applications. All operating parameters must be validated for each customer application by the customer. Should the buyer use Vishay Semiconductors products for any unintended or unauthorized application, the buyer shall indemnify Vishay Semiconductors against all claims, costs, damages, and expenses, arising out of, directly or indirectly, any claim of personal damage, injury or death associated with such unintended or unauthorized use.

Vishay Semiconductor GmbH, P.O.B. 3535, D-74025 Heilbronn, Germany



Notice

Specifications of the products displayed herein are subject to change without notice. Vishay Intertechnology, Inc., or anyone on its behalf, assumes no responsibility or liability for any errors or inaccuracies.

Information contained herein is intended to provide a product description only. No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document. Except as provided in Vishay's terms and conditions of sale for such products, Vishay assumes no liability whatsoever, and disclaims any express or implied warranty, relating to sale and/or use of Vishay products including liability or warranties relating to fitness for a particular purpose, merchantability, or infringement of any patent, copyright, or other intellectual property right.

The products shown herein are not designed for use in medical, life-saving, or life-sustaining applications. Customers using or selling these products for use in such applications do so at their own risk and agree to fully indemnify Vishay for any damages resulting from such improper use or sale.